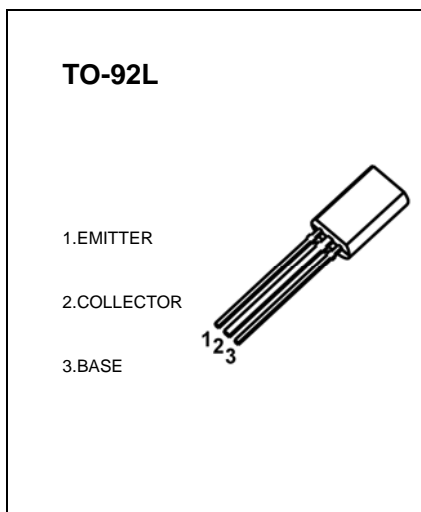


# TO-92L Plastic-Encapsulate Transistors

## KSA928A TRANSISTOR(PNP)

### FEATURE

- Audio Power Amplifier
- Complement to Application



### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-2	A
P <sub>C</sub>	Collector Power Dissipation	0.75	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55 to +150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Type	Max	Unit
Collector-base breakdown voltage	V(BR) <sub>CB0</sub>	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-30			V
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> =0	-30			V
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> = -1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -30V, I <sub>E</sub> =0			-0.1	μ A
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-0.1	μ A
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> = -500mA	100		320	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -1.5 A, I <sub>B</sub> = -0.03A			-2	V
Base-emitter voltage	V <sub>BE</sub>	I <sub>C</sub> = -500 mA, V <sub>CE</sub> = -2V			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -500mA		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		48		pF

### CLASSIFICATION OF h<sub>FE</sub>

Rank	O	Y
Range	100-200	160-320